



STD25NF10

N-channel 100V - 0.033Ω - 25A - DPAK
Low gate charge STripFET™ II Power MOSFET

General features

Type	V _{DSS}	R _{DS(on)}	I _D
STD25NF10	100V	< 0.038Ω	25A

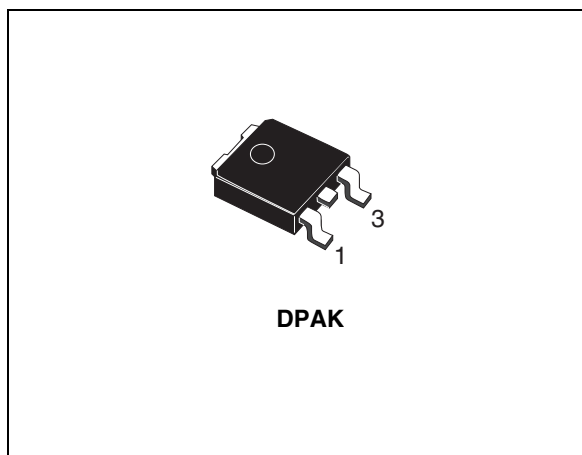
- Exceptional dv/dt capability
- Application oriented characterization
- 100% avalanche tested
- Application oriented characterization

Description

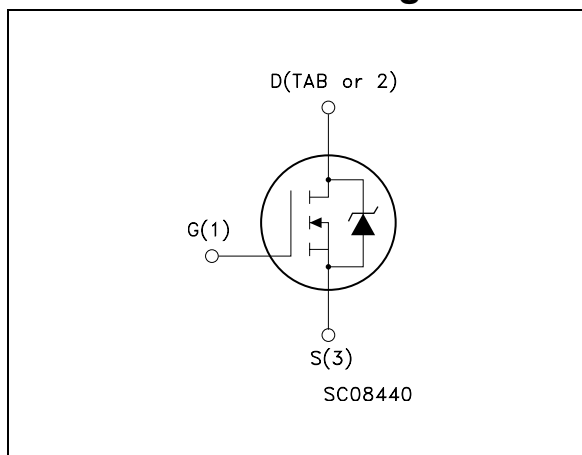
This Power MOSFET series realized with STMicroelectronics unique STripFET process has specifically been designed to minimize input capacitance and gate charge. It is therefore suitable as primary switch in advanced high-efficiency isolated DC-DC converters for Telecom and Computer application. It is also intended for any application with low gate charge drive requirements.

Applications

- Switching application



Internal schematic diagram



Order codes

Part number	Marking	Package	Packaging
STD25NF10T4	D25NF10	DPAK	Tape & reel

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1 Electrical ratings

Table 1. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage ($V_{GS} = 0$)	100	V
V_{DGR}	Drain-gate voltage ($R_{GS} = 20\text{ k}\Omega$)	100	V
V_{GS}	Gate- source voltage	± 20	V
$I_D^{(1)}$	Drain current (continuous) at $T_C = 25^\circ\text{C}$	25	A
I_D	Drain current (continuous) at $T_C = 100^\circ\text{C}$	21	A
$I_{DM}^{(2)}$	Drain current (pulsed)	100	A
P_{tot}	Total dissipation at $T_C = 25^\circ\text{C}$	100	W
	Derating Factor	0.67	W/°C
$dv/dt^{(3)}$	Peak diode recovery avalanche energy	13	V/ns
$E_{AS}^{(4)}$	Single pulse avalanche energy	480	mJ
T_{stg}	Storage temperature	-55 to 175	°C
T_j	Max. operating junction temperature		

1. Current limited by package
2. Pulse width limited by safe operating area.
3. $I_{SD} \leq 35\text{A}$, $di/dt \leq 300\text{A}/\mu\text{s}$, $V_{DD} = V_{(BR)DSS}$, $T_j \leq T_{JMAX}$
4. Starting $T_j = 25^\circ\text{C}$, $I_D = 12.5\text{A}$ $V_{DD} = 50\text{V}$

Table 2. Thermal data

$R_{thj-case}$	Thermal resistance junction-case max	1.5	°C/W
$R_{thj-amb}$	Thermal resistance junction-to ambient max	100	°C/W
T_J	Maximum lead temperature for soldering purpose	300	°C

2 Electrical characteristics

($T_{CASE}=25^{\circ}C$ unless otherwise specified)

Table 3. On/off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$I_D = 250\mu A, V_{GS} = 0$	100			V
I_{DSS}	Zero gate voltage drain current ($V_{GS} = 0$)	$V_{DS} = \text{Max rating}$ $V_{DS} = \text{Max rating},$ $T_C = 125^{\circ}C$			1 10	μA μA
I_{GSS}	Gate-body leakage current ($V_{DS} = 0$)	$V_{GS} = \pm 20V$			± 100	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}, I_D = 250\mu A$	2	3	4	V
$R_{DS(on)}$	Static drain-source on resistance	$V_{GS} = 10V, I_D = 12.5A$		0.033	0.038	Ω

Table 4. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$g_{fs}^{(1)}$	Forward transconductance	$V_{DS} = 15V, I_D = 12.5A$		20		S
C_{iss} C_{oss} C_{rss}	Input capacitance Output capacitance Reverse transfer capacitance	$V_{DS} = 25V, f = 1MHz,$ $V_{GS} = 0$		1550 220 95		pF pF pF
$t_{d(on)}$ t_r $t_{d(off)}$ t_f	Turn-on delay time Rise time Turn-off delay time Fall time	$V_{DD} = 50V, I_D = 12.5A$ $R_G = 4.7\Omega, V_{GS} = 10V$ (see Figure 12)		17 60 60 15		ns ns ns ns
Q_g Q_{gs} Q_{gd}	Total gate charge Gate-source charge Gate-drain charge	$V_{DD} = 80V, I_D = 12.5A,$ $V_{GS} = 10V, R_G = 4.7\Omega$ (see Figure 13)		55 12 20		nC nC nC

1. Pulsed: Pulse duration = 300 μs , duty cycle 1.5 %.

Table 5. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD} $I_{SDM}^{(1)}$	Source-drain current Source-drain current (pulsed)				25 100	A A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 25A, V_{GS} = 0$			1.5	V
t_{rr} Q_{rr} I_{RRM}	Reverse recovery time Reverse recovery charge Reverse recovery current	$I_{SD} = 25A, di/dt = 100A/\mu s,$ $V_{DD} = 50V, T_j = 150^\circ C$ (see Figure 14)		88 317 7.2		ns nC A

1. Pulse width limited by safe operating area.
2. Pulsed: Pulse duration = 300 μs , duty cycle 1.5 %

2.1 Electrical characteristics (curves)

Figure 1. Safe operating area

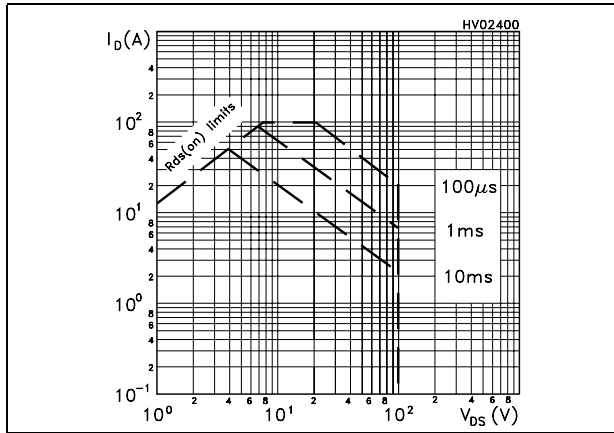


Figure 2. Thermal impedance

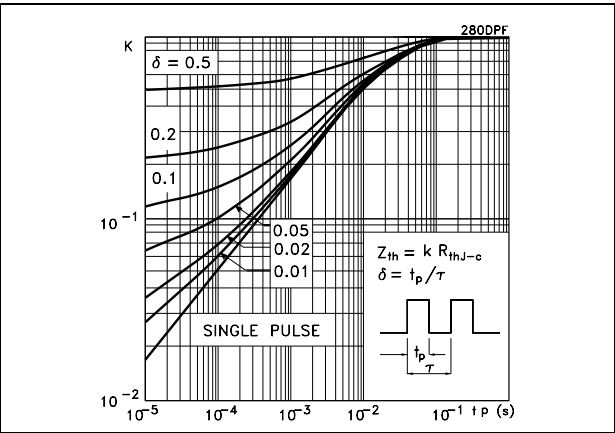


Figure 3. Output characteristics

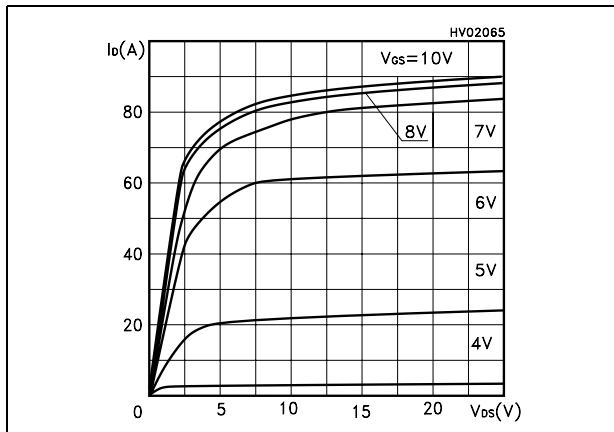


Figure 4. Transfer characteristics

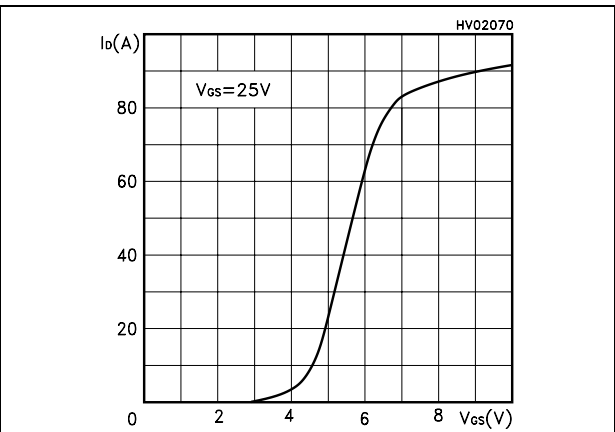


Figure 5. Transconductance

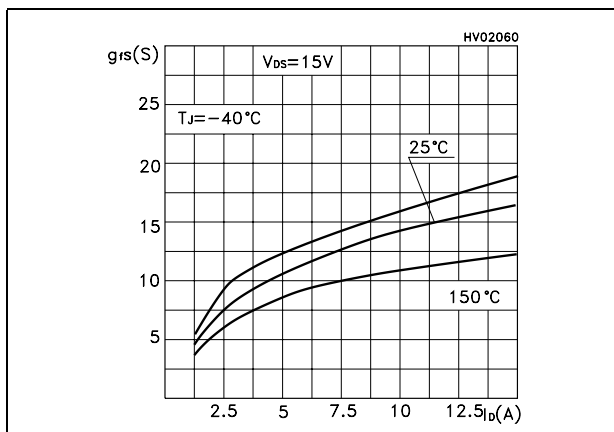


Figure 6. Static drain-source on resistance

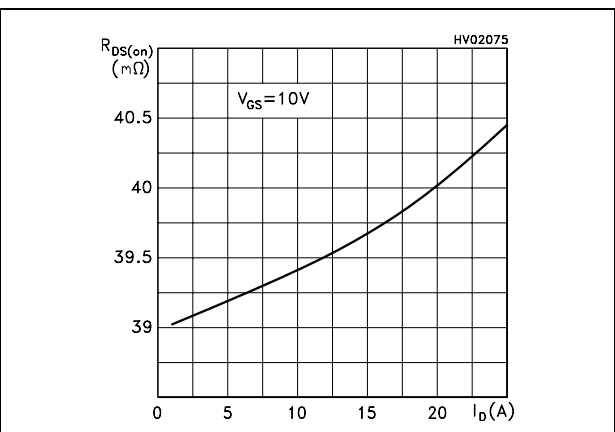


Figure 7. Gate charge vs gate-source voltage Figure 8. Capacitance variations

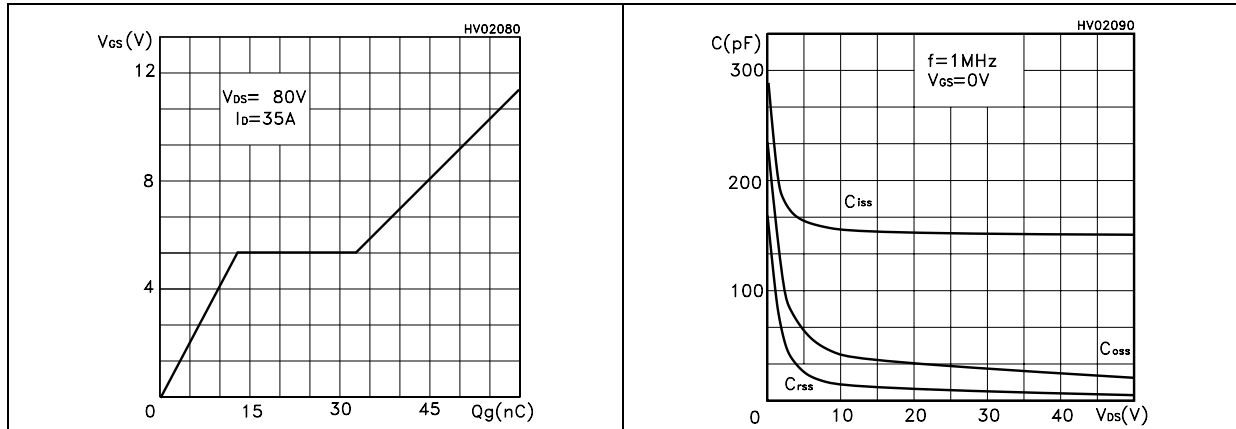


Figure 9. Normalized gate threshold voltage vs temperature Figure 10. Normalized on resistance vs temperature

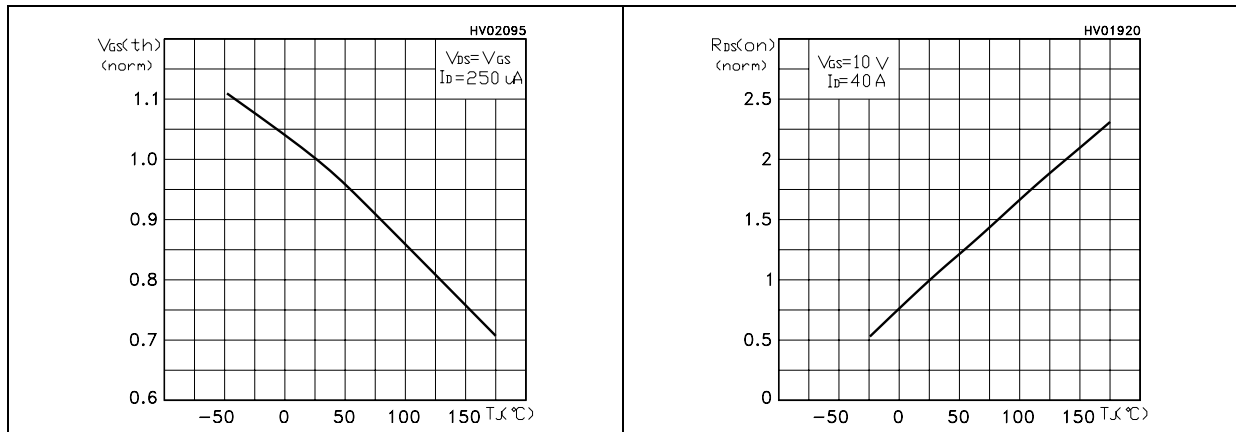
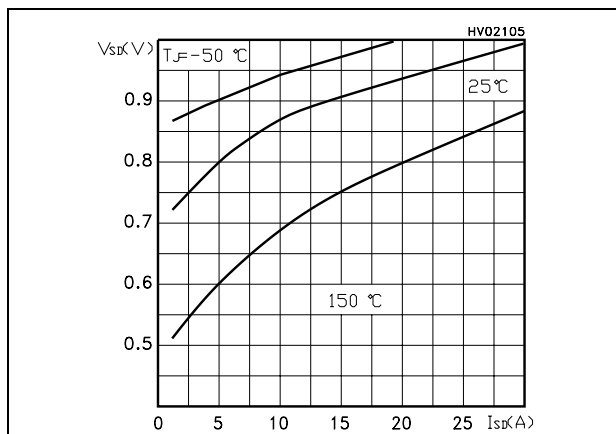


Figure 11. Source-drain diode forward characteristics



3 Test circuit

Figure 12. Switching times test circuit for resistive load



Figure 13. Gate charge test circuit

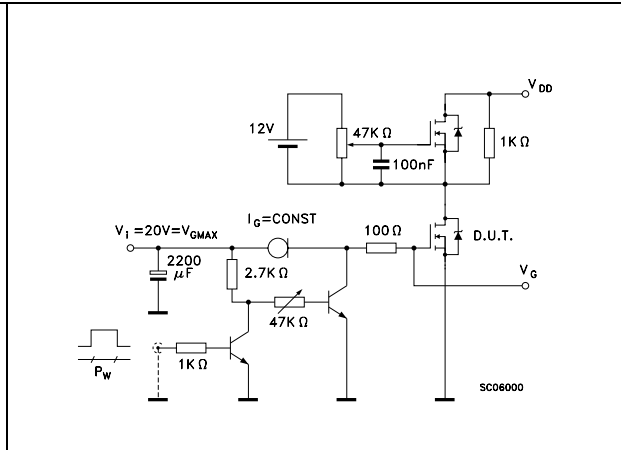


Figure 14. Test circuit for inductive load switching and diode recovery times



Figure 15. Unclamped Inductive load test circuit

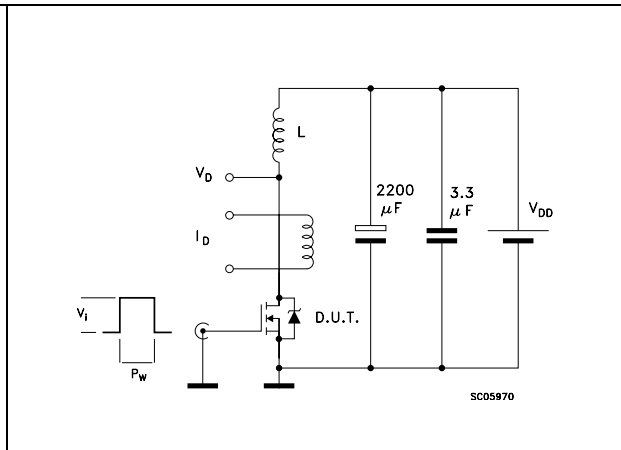
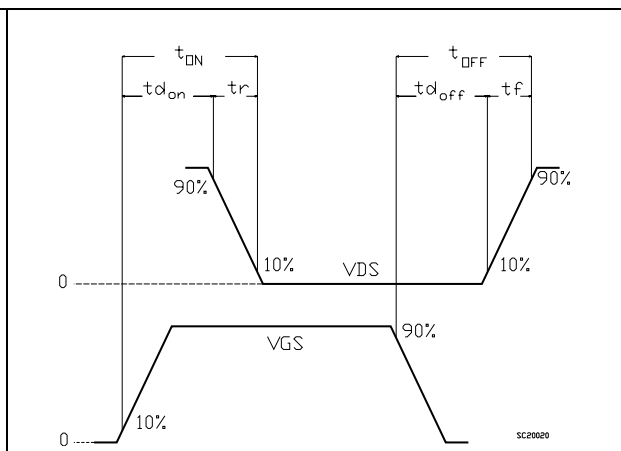


Figure 16. Unclamped inductive waveform



Figure 17. Switching time waveform

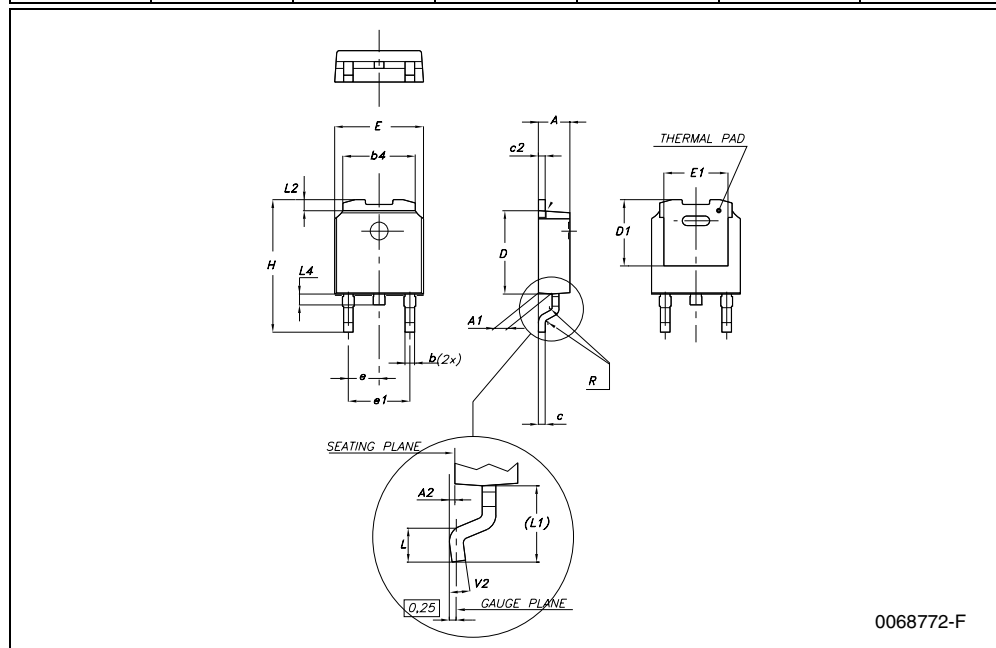


4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect . The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com

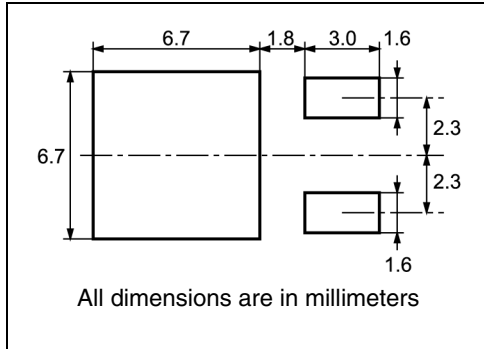
DPAK MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A	2.2		2.4	0.086		0.094
A1	0.9		1.1	0.035		0.043
A2	0.03		0.23	0.001		0.009
B	0.64		0.9	0.025		0.035
b4	5.2		5.4	0.204		0.212
C	0.45		0.6	0.017		0.023
C2	0.48		0.6	0.019		0.023
D	6		6.2	0.236		0.244
D1		5.1			0.200	
E	6.4		6.6	0.252		0.260
E1		4.7			0.185	
e		2.28			0.090	
e1	4.4		4.6	0.173		0.181
H	9.35		10.1	0.368		0.397
L	1			0.039		
(L1)		2.8			0.110	
L2		0.8			0.031	
L4	0.6		1	0.023		0.039
R		0.2			0.008	
V2	0°		8°	0°		8°



5 Packing mechanical data

DPAK FOOTPRINT



TAPE AND REEL SHIPMENT

40 mm min. Access hole at slot location

Full radius

Tape slot in core for tape start 2.5mm min. width

G measured at hub

REEL MECHANICAL DATA

DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A		330		12.992
B	1.5		0.059	
C	12.8	13.2	0.504	0.520
D	20.2		0.795	
G	16.4	18.4	0.645	0.724
N	50		1.968	
T		22.4		0.881

TAPE MECHANICAL DATA

DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A0	6.8	7	0.267	0.275
B0	10.4	10.6	0.409	0.417
B1		12.1		0.476
D	1.5	1.6	0.059	0.063
D1	1.5		0.059	
E	1.65	1.85	0.065	0.073
F	7.4	7.6	0.291	0.299
K0	2.55	2.75	0.100	0.108
P0	3.9	4.1	0.153	0.161
P1	7.9	8.1	0.311	0.319
P2	1.9	2.1	0.075	0.082
R	40		1.574	
W	15.7	16.3	0.618	0.641

TOP COVER TAPE

User Direction of Feed

Center line of cavity

Bending radius R min.

FEED DIRECTION

TRL

For machine ref. only including draft and radii concentric around B0

10 pitches cumulative tolerance on tape +/- 0.2 mm

6 Revision history

Table 6. Revision history

Date	Revision	Changes
21-Jun-2004	3	Preliminary version
03-Jul-2006	4	New template, no content change

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